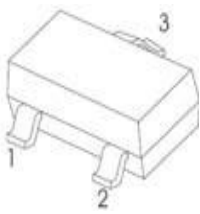
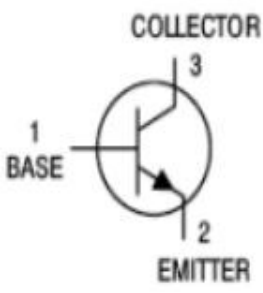


TRANSISTOR (PNP)	SOT-23 Plastic-Encapsulate Transistors		
<p><u>SOT-23</u></p>   <p>1.BASE 2.EMITTER 3.COLLECTOR</p> <p>Marking :2L</p>	<p>Features</p> <ul style="list-style-type: none"> ※ Complimentary to MMBT5551 ※ Collector Current: $I_c=0.6A$ ※ Ideal for Medium Power Amplification and Switching 		
MAXIMUM RATINGS (Ta=25°C unless otherwise noted)			
Parameter	Symbol	Value	Unit
Collector-Base Voltage	VCBO	-160	V
Collector-Emitter Voltage	VCEO	-150	V
Emitter-Base Voltage	VEBO	-6	V
Collector Current	IC	-600	mA
Collector Power Dissipation	PC	450	mW
Thermal Resistance From Junction To Ambient	ROJA	625	°C/W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55~+150	°C

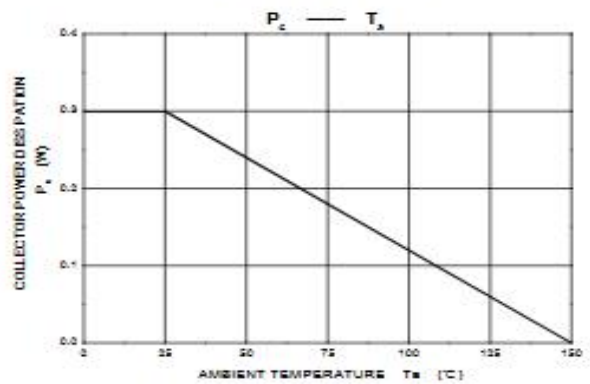
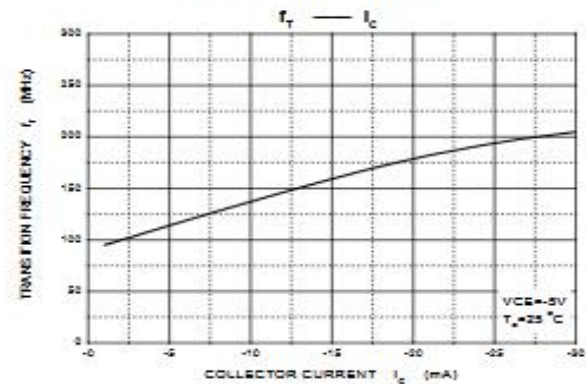
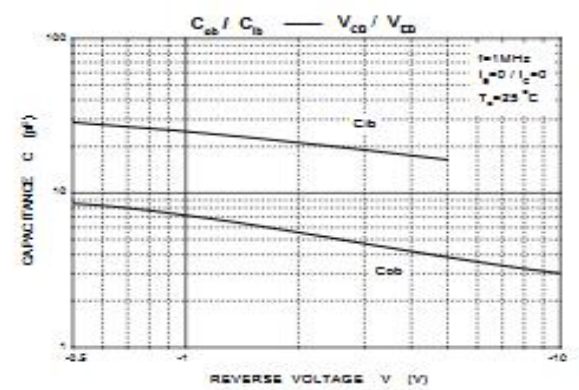
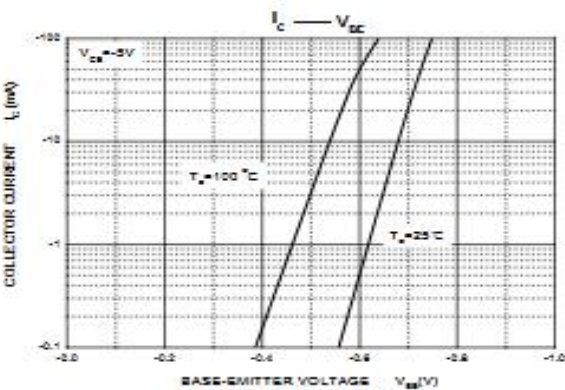
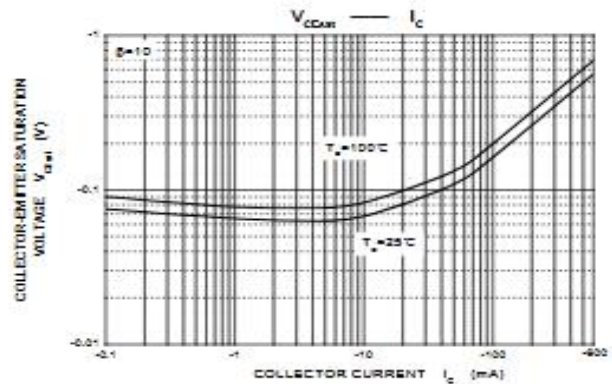
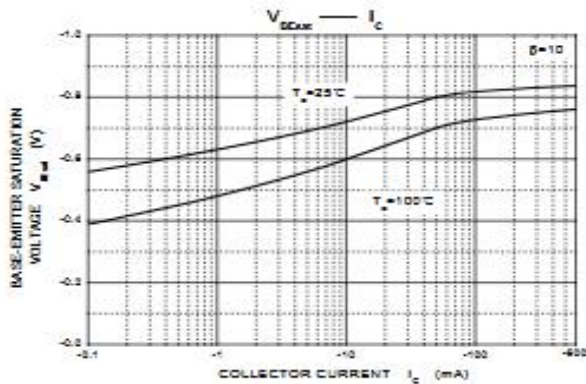
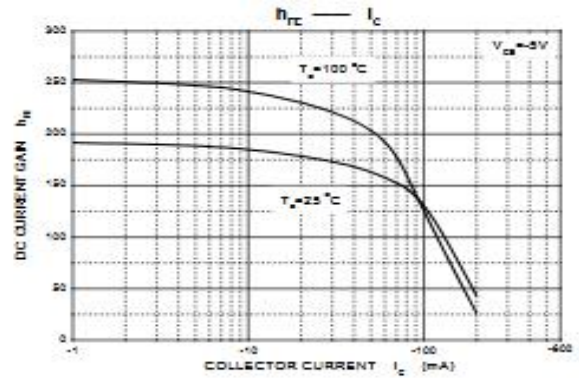
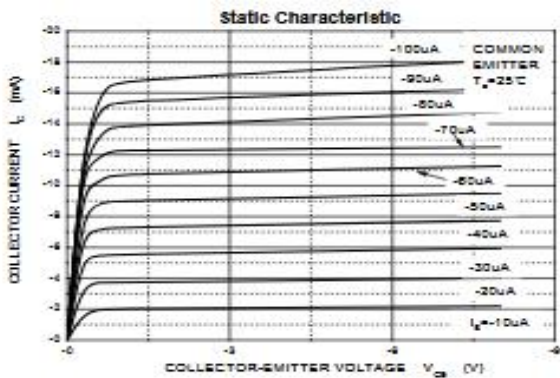
ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	IC= -100μA, IE=0	-160	-255	-500	V
Collector-emitter breakdown voltage	V(BR)CEO	IC= -1mA, IB=0	-150	-251	-500	V
Emitter-base breakdown voltage	V(BR)EBO	IE= -10μA, IC=0	-6	-11	-30	V
Collector cut-off current	ICBO	VCB= -120 V , IE=0			-0.1	μ A
Collector cut-off current	ICEO	VCB= -150V , IE=0			-1.8	μ A
Emitter cut-off current	IEBO	VEB= -4V , IC=0			-0.1	μ A
DC current gain	hFE	VCE=-5V, IC= -1mA	80			
	hFE	VCE=-5V, IC= -10mA	100		200	
	hFE	VCE=-5V, IC= -50mA	50			
Collector-emitter saturation voltage	VCE(sat)	IC= -50 mA, IB= -5mA			-0.5	V
Base-emitter saturation voltage	VBE(sat)	IC= -50 mA, IB= -5mA			-1.	V
Transition frequency	fT	VCE=6V, IC= 20mA f=30MHz	100		300	MHz

CLASSIFICATION OF hFE

Rank	L	H
Range	100-200	200-300
MARKING	2L	

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



单击下面可查看定价，库存，交付和生命周期等信息

[>>DIOS\(迪恩思\)](#)